



STP80N70F4

N-channel 68 V, 8.2 mΩ typ., 85 A STripFET™ DeepGATE™
Power MOSFET in TO-220 package

Datasheet — production data

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STP80N70F4	68 V	< 9.8 mΩ	85 A

- N-channel enhancement mode
- 100% avalanche rated
- Low gate charge
- Very low on-resistance

Application

Switching applications

Description

This device is an N-channel Power MOSFET developed using ST's STripFET™ DeepGATE™ technology. The device has a new gate structure and is specially designed to minimize on-state resistance to provide superior switching performance.

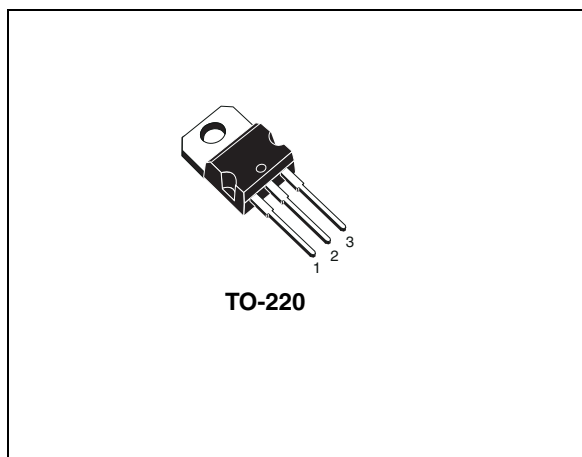


Figure 1. Internal schematic diagram

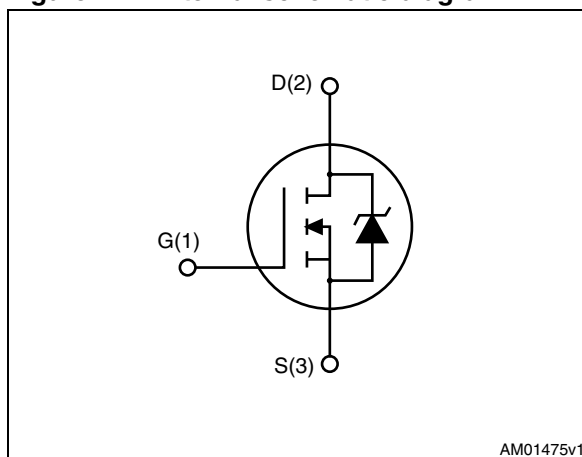


Table 1. Device summary

Order code	Marking	Package	Packaging
STP80N70F4	80N70F4	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Revision history	11

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	68	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	85	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	60	A
$I_{DM}^{(1)}$	Drain current (pulsed)	340	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
	Derating factor	1	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	185	mJ
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Pulse width limited by safe operating area

2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 35\text{ A}$, $V_{DD} = 34\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	$^\circ\text{C/W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C/W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	68			V
I_{DSS}	Zero gate voltage	$V_{DS} = 68\ \text{V}$			1	μA
	Drain current ($V_{GS} = 0$)	$V_{DS} = 68\ \text{V}$, $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$, $I_D = 40\ \text{A}$		8.2	9.8	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			5600		pF
C_{oss}	Output capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$	-	430	-	pF
C_{rss}	Reverse transfer capacitance				250	
Q_g	Total gate charge	$V_{DD} = 34\ \text{V}$, $I_D = 80\ \text{A}$, $V_{GS} = 10\ \text{V}$ <i>(see Figure 14)</i>	-	90	-	nC
Q_{gs}	Gate-source charge			25	-	nC
Q_{gd}	Gate-drain charge				23	

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 34\ \text{V}$, $I_D = 40\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ <i>(see Figure 13)</i>	-	25	-	ns	
t_r	Rise time				36		ns
$t_{d(off)}$	Turn-off-delay time			-	80	-	ns
t_f	Fall time			25		ns	

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		85	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		340	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 85 \text{ A}, V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 80 \text{ A},$ $V_{DD} = 54.4 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150 \text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	55		ns
Q_{rr}	Reverse recovery charge			130		nC
I_{RRM}	Reverse recovery current			4		A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

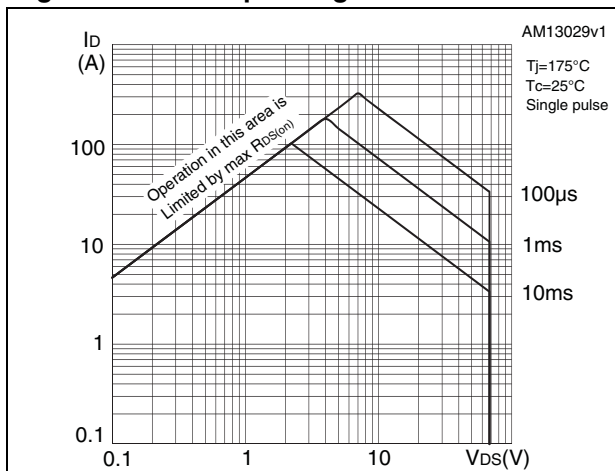


Figure 3. Thermal impedance

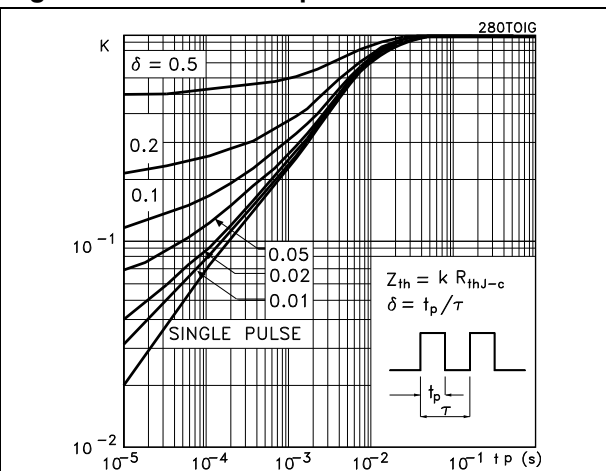


Figure 4. Output characteristics

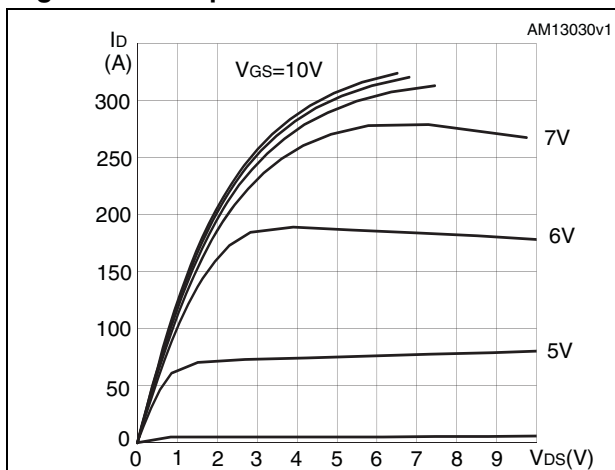


Figure 5. Transfer characteristics

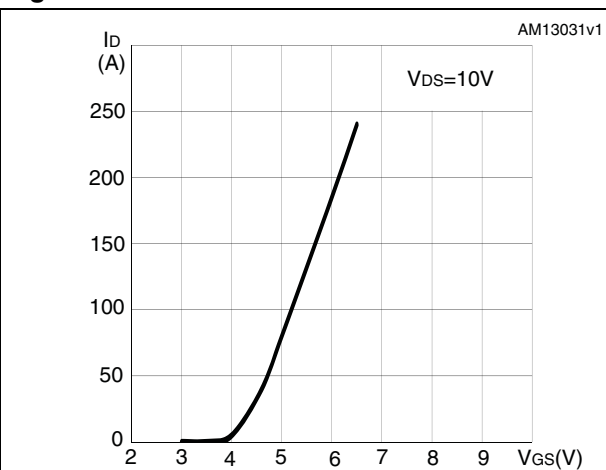


Figure 6. Normalized BV_{DSS} vs temperature

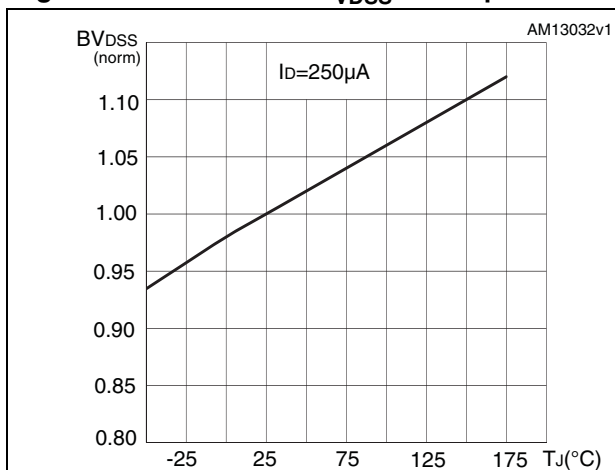


Figure 7. Static drain-source on-resistance

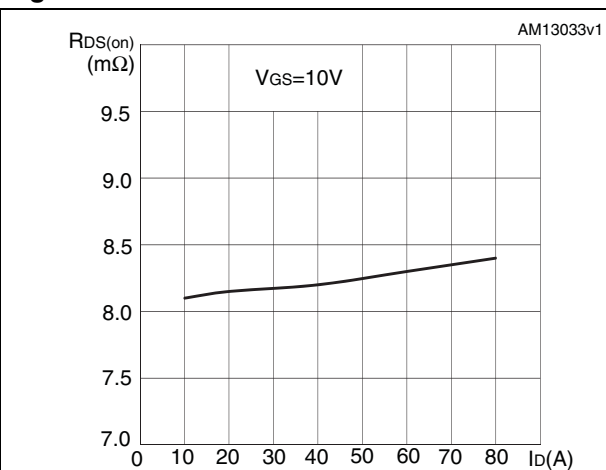


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

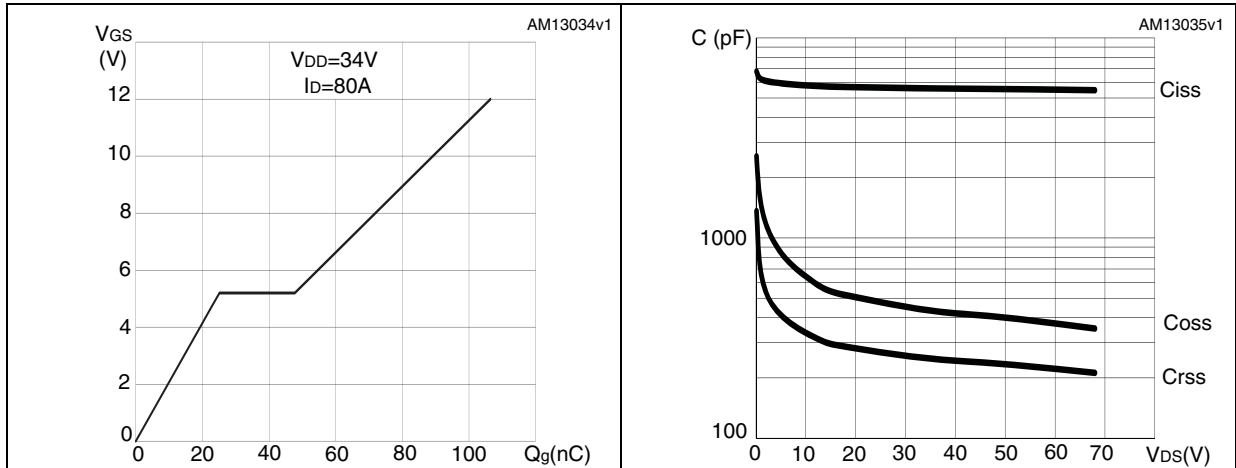


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature

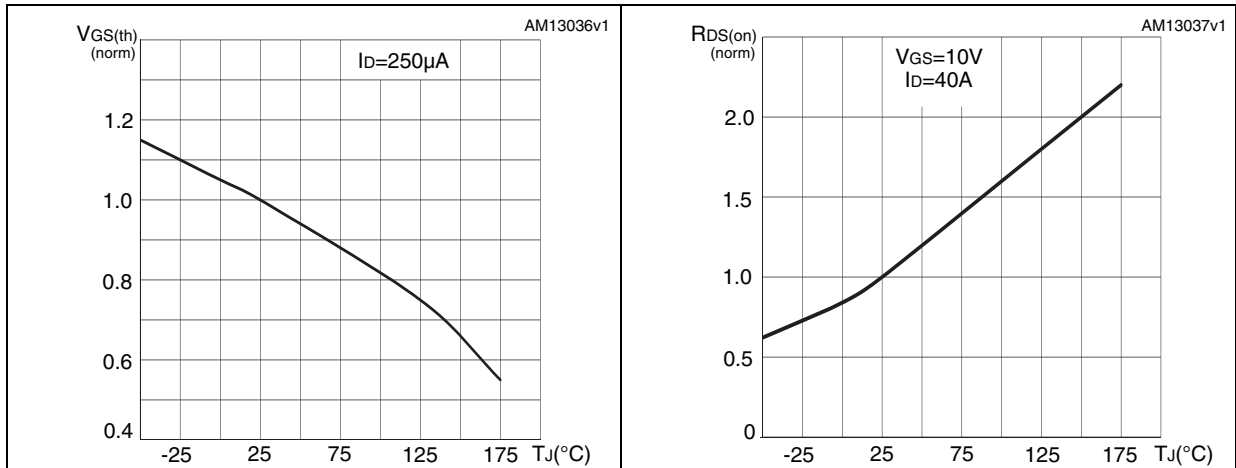
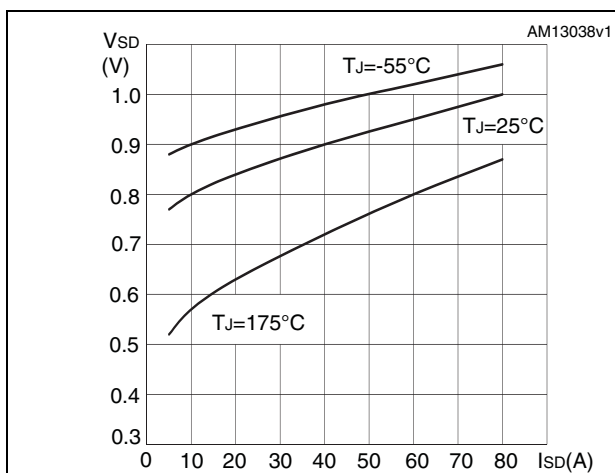
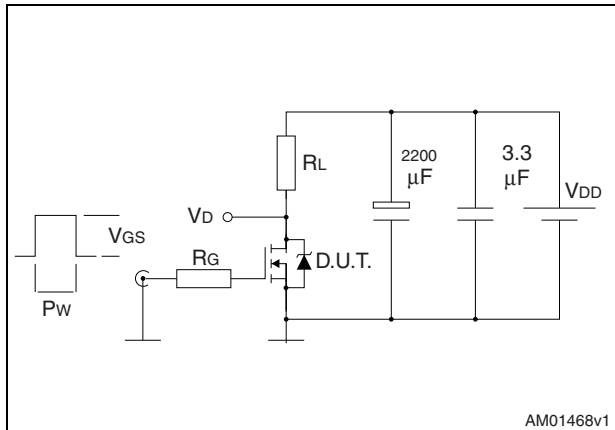


Figure 12. Source-drain diode forward characteristics



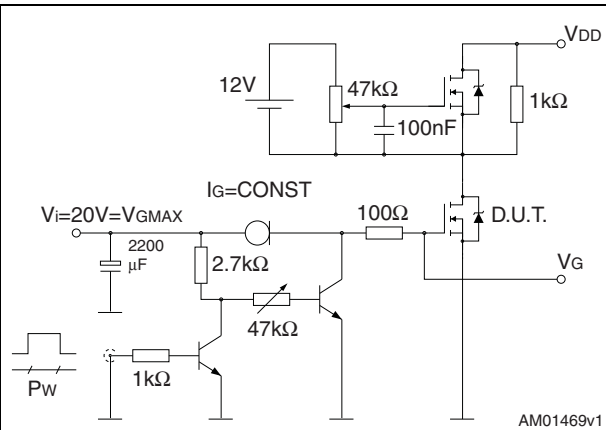
3 Test circuits

Figure 13. Switching times test circuit for resistive load



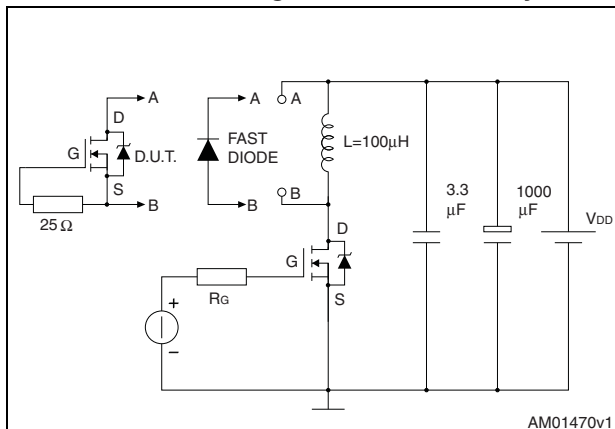
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Figure 14. Gate charge test circuit



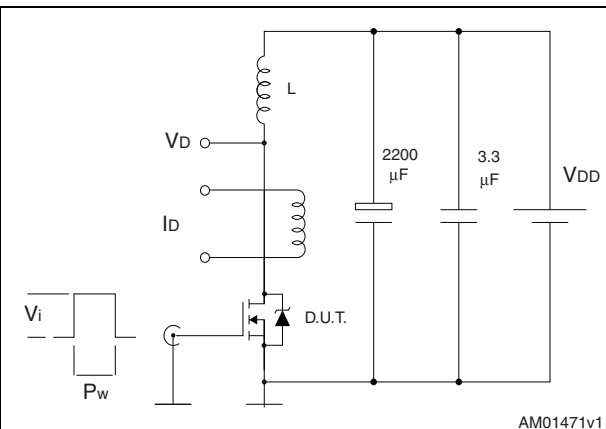
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Figure 15. Test circuit for inductive load switching and diode recovery times



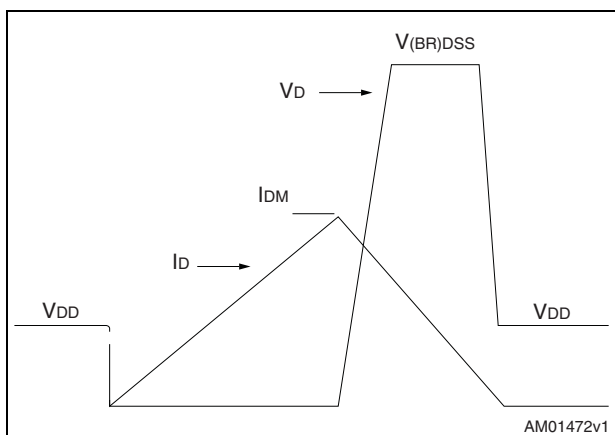
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Figure 16. Unclamped inductive load test circuit



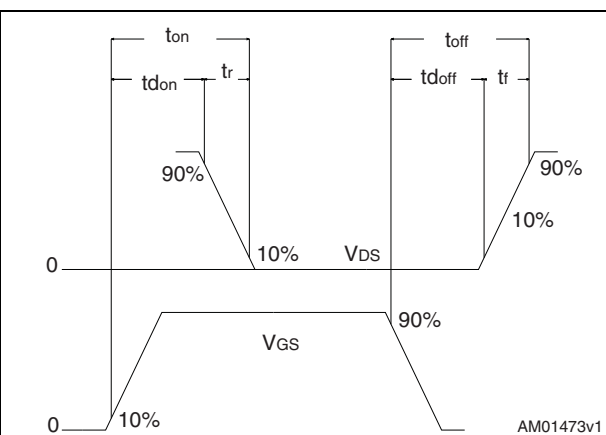
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



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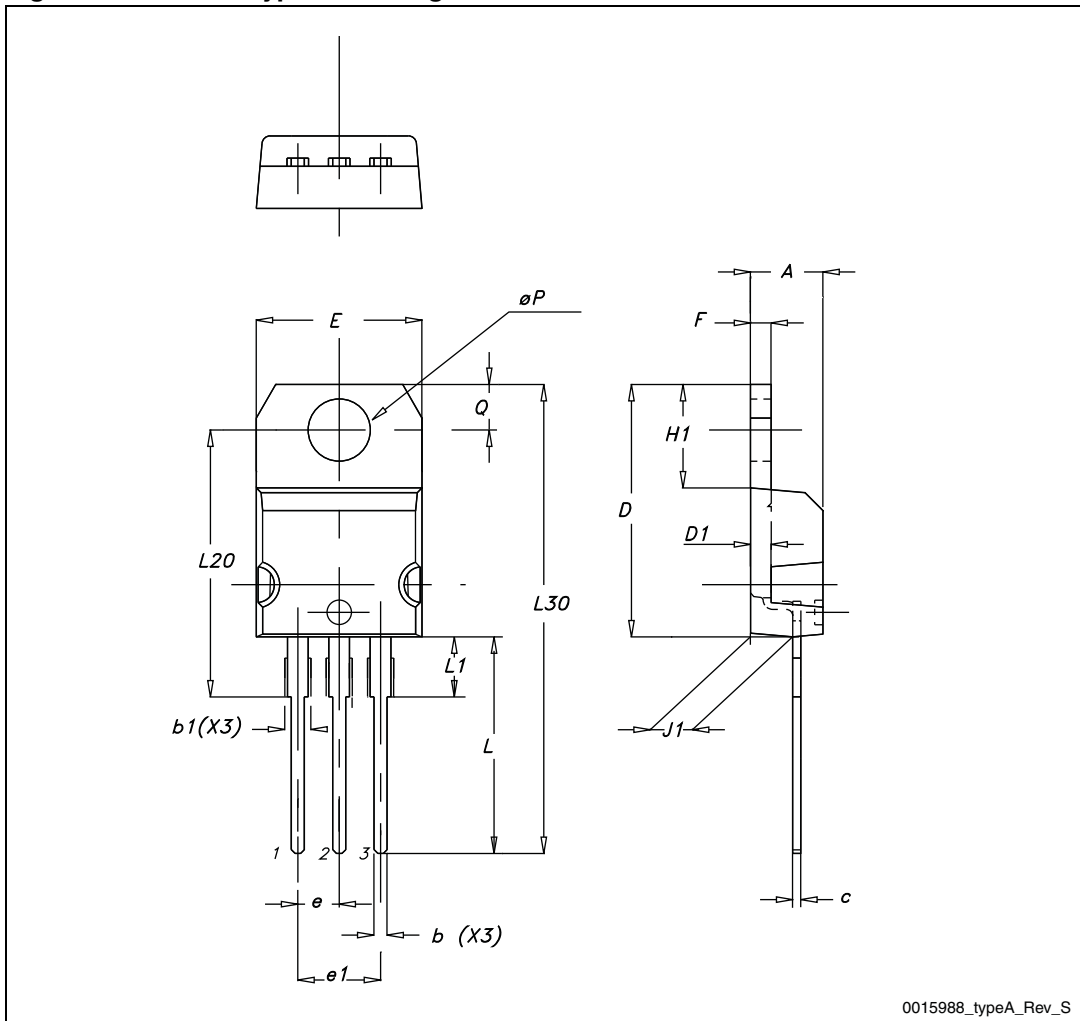
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
12-Jan-2011	1	First release.
17-Dec-2012	2	Document status promoted from preliminary data to production data. Section 2.1: Electrical characteristics (curves) has been added.

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